(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
14 October 2010 (14.10.2010)

PCT

(10) International Publication Number
WO 2010/117405 A3

(51) International Patent Classification:
H01L 21/8247 (2006.01) *H01L 21/205* (2006.01)

(21) International Application Number:
PCT/US2010/000733

(22) International Filing Date:
11 March 2010 (11.03.2010)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
12/419,779 7 April 2009 (07.04.2009) US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report (Art. 21(3))*

— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments (Rule 48.2(h))*

[Continued on next page]

(54) Title: SEMICONDUCTOR PROCESSING

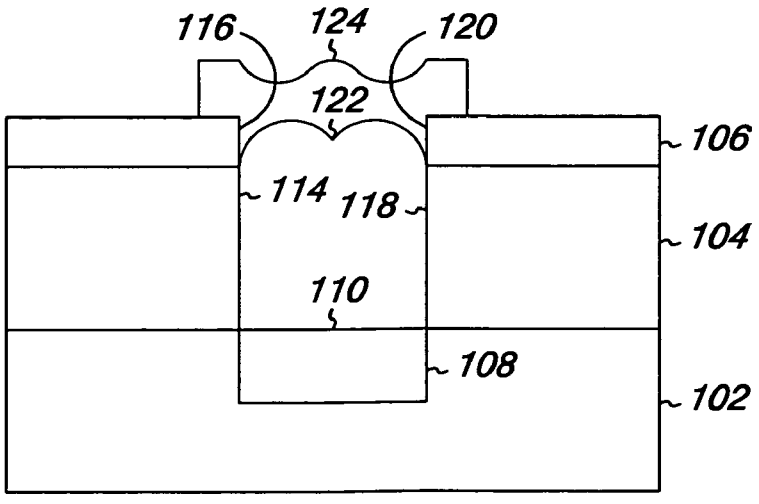


Fig. 1E

(57) Abstract: Devices, methods, and systems for semiconductor processing are described herein. A number of method embodiments of semiconductor processing can include forming a silicon layer on a structure, forming an opening through the silicon layer and into the structure, and selectively forming a resistance variable material in the opening such that the resistance variable material does not form on the silicon layer.

WO 2010/117405 A3

(88) Date of publication of the international search report:
16 December 2010